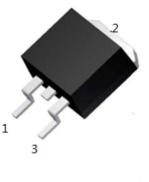


FRED Ultrafast Soft Recovery Diode, 30A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary	
VR	400 V
lf(AV)	30A
trr	25 ns

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		400	V
Continuous forward current	lf(AV)	Tc =110°C	30	
Single pulse forward current	Ifsm	Tc =25°C	175	A
Maximum repetitive forward current	Ifrm	Square wave, 20kHZ	55	
Operating junction	Tj		175	°C
Storage temperatures	Tstg		-55 to +175	°C

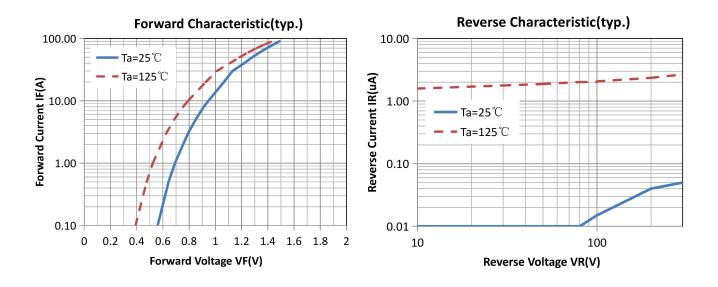


Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage Blocking voltage	Vbr, Vr	Ir=100#A	400			
Forward voltage (Per Diode)		IF=30A		1.15	1.50	V
	VF	IF=30A, Tj =125°C		1.0	1.40	
Reverse leakage	_	Vr= Vrrm			20	
current(Per Diode)	Tj=150°C, Vr=400V			200	μA	
Reverse recovery time(Per Diode)		I _F =0.5A, I _R =1A, I _{RR} =0.25A		35	55	
	Trr	I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us		25	35	ns

Thermal characteristics

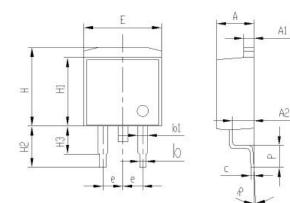
Paramter	Symbol	Тур	Units
Junction-to-Case	R _{θJC}	0.8	°C/W

Electrical performance (typic)





Package Information





SA

Symbol	Dimensions(millimeters)		
Symbol	Min.	Max.	
А	4.50	4.90	
A1	1.17	1.37	
A2	2.40	2.80	
b	0.60	1.00	
b1	0.95	1.35	
С	0.26	0.50	
е	2.34	2.74	
E	9.70	10.1	
Н	9.80	10.2	
H1	8.50	8.90	
H2	5.05	5.45	
H3	3.60	4.00	
R	0°	6°	
Р	2.55	2.95	